

## DESCRIPTION

The MX0205 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

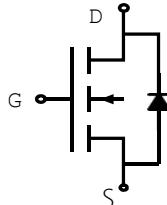
## GENERAL FEATURES

- $V_{DS} = 60V$ ,  $I_D = 2.8A$
- $R_{DS(ON)} < 100m\Omega$  @  $V_{GS} = 10V$
- $R_{DS(ON)} < 115m\Omega$  @  $V_{GS} = 4.5V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

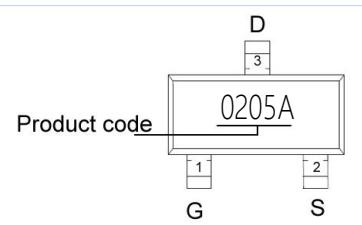
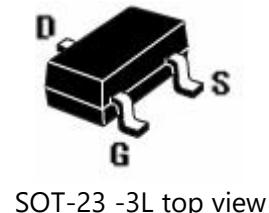
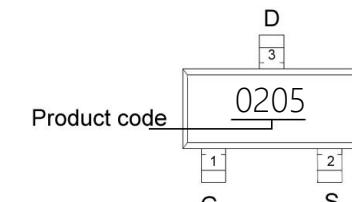
## APPLICATION

- Battery Switch
- DC/DC Converter

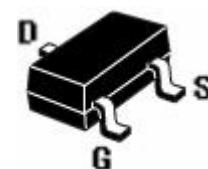
## PINOUT



Schematic diagram



Marking and pin Assignment



SOT-23 top view

## ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	2.8	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	10	A
Maximum Power Dissipation	$P_D$	1.7	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C
Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	73.5	°C/W

Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.


**ELECTRICAL CHARACTERISTICS**(TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
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**Off Characteristics**

Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA

**On Characteristics** <sup>(Note 3)</sup>

Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	1.0	1.5	V
Drain-Source Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =2.8A	-	87	100	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.8A	-	95	115	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =2A	-	130	150	mΩ

**Dynamic Characteristics** <sup>(Note 4)</sup>

Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, F=1.0MHz	-	247	-	PF
Output Capacitance	C <sub>oss</sub>		-	34	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	19.5	-	PF

**Switching Characteristics** <sup>(Note 4)</sup>

Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =1.5A V <sub>GS</sub> =10V, R <sub>GEN</sub> =1Ω	-	6	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	15	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	15	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V, I <sub>D</sub> =2.5A, V <sub>GS</sub> =4.5V	-	6	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	1.3	-	nC

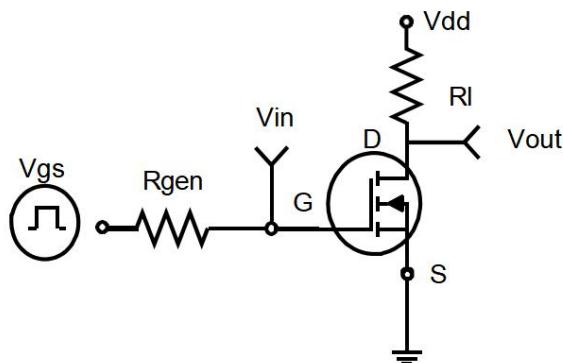
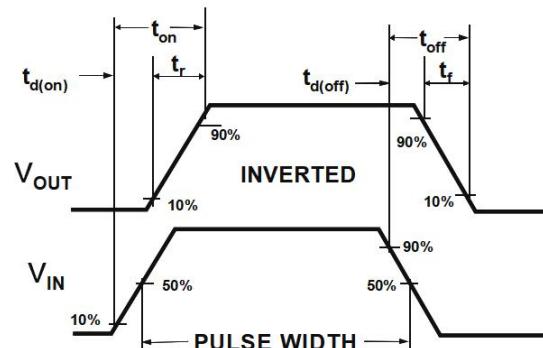
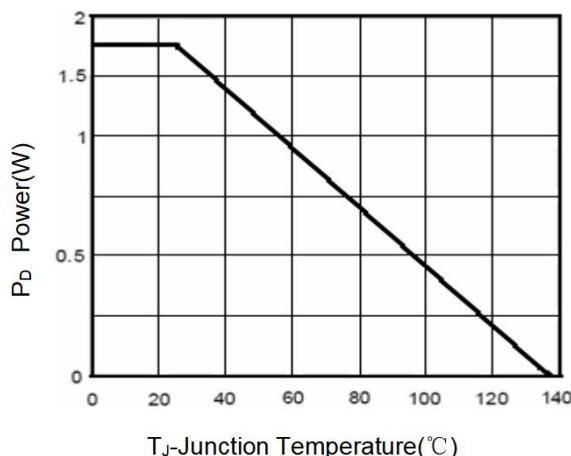
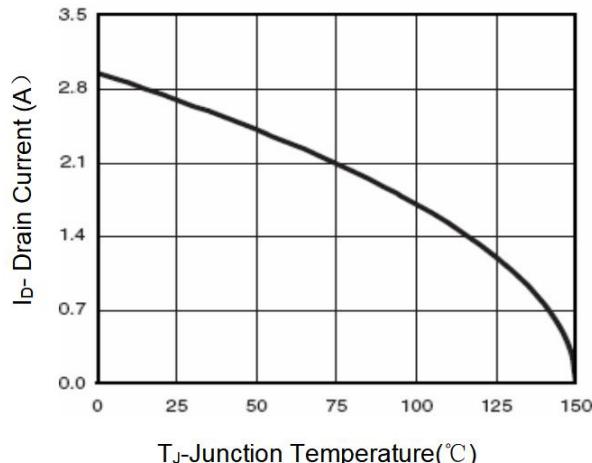
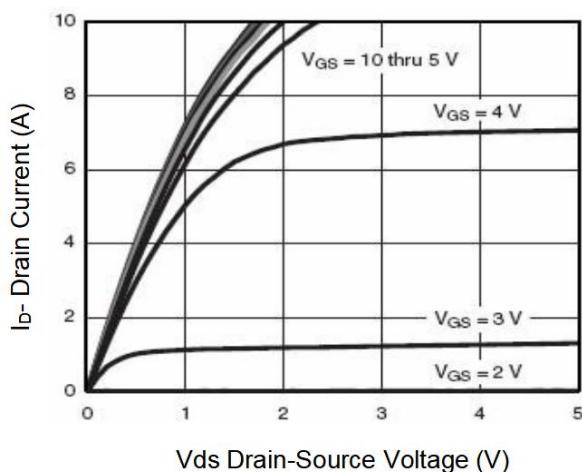
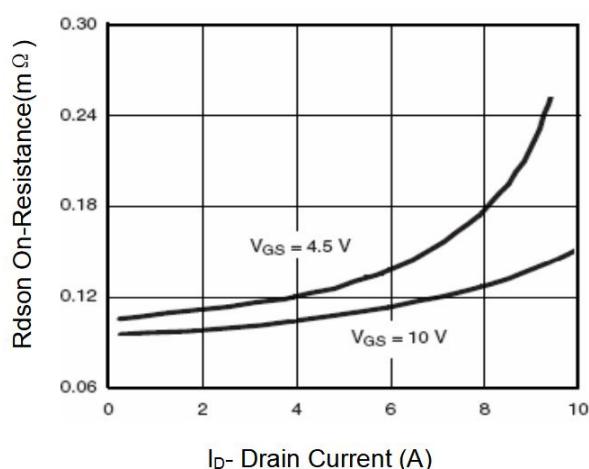
**Drain-Source Diode Characteristics**

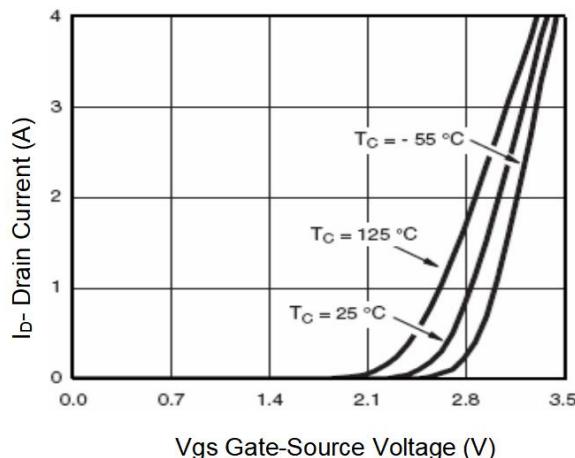
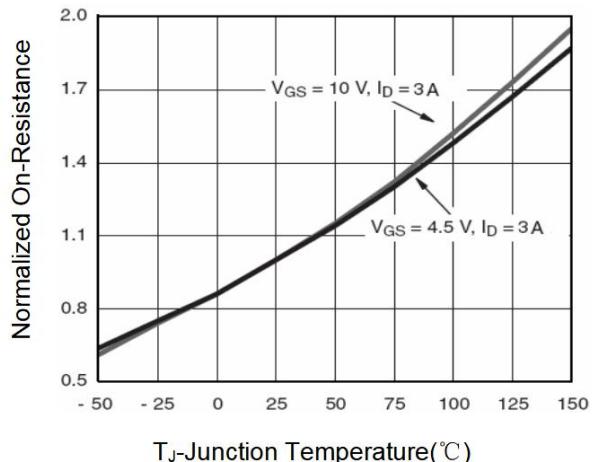
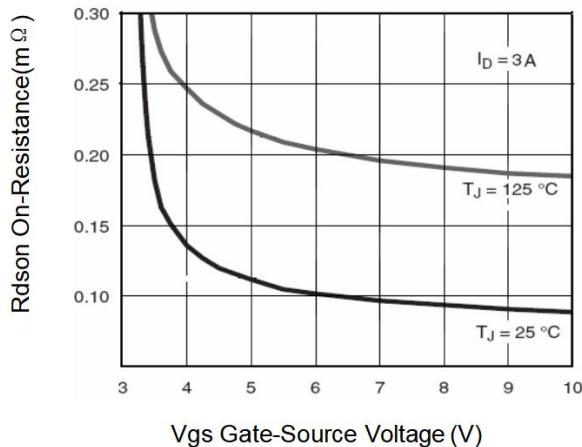
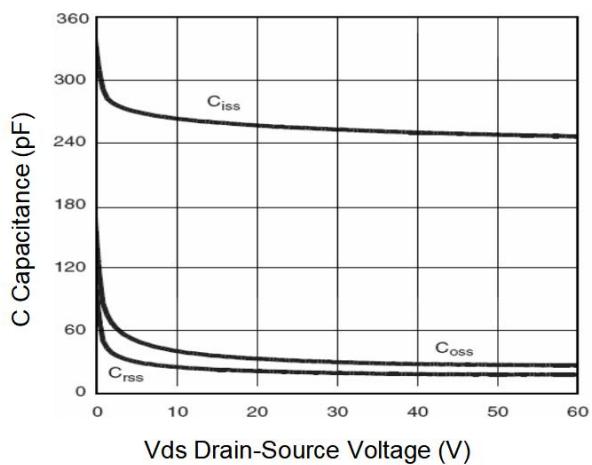
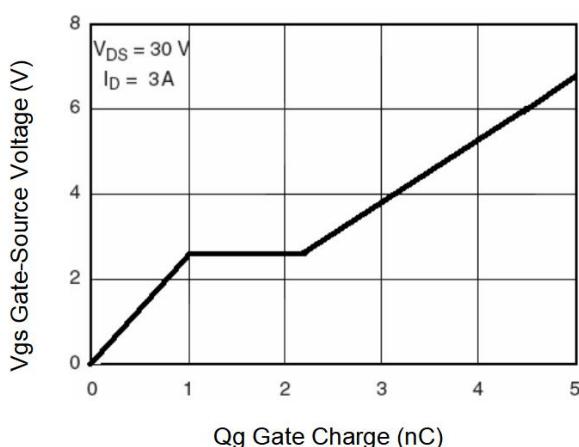
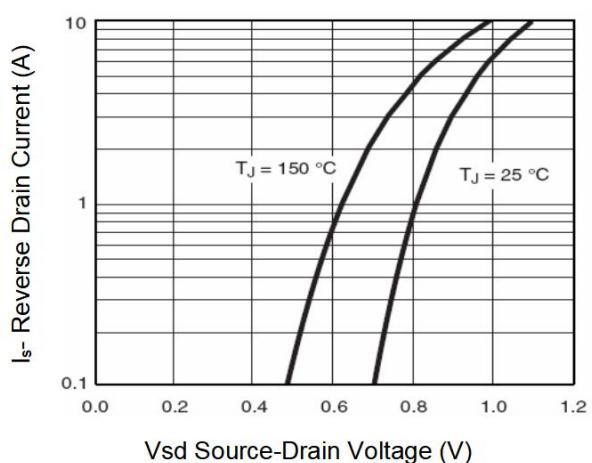
Diode Forward Voltage <sup>(Note 3)</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =2.5A	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	I <sub>S</sub>		-	-	3	A

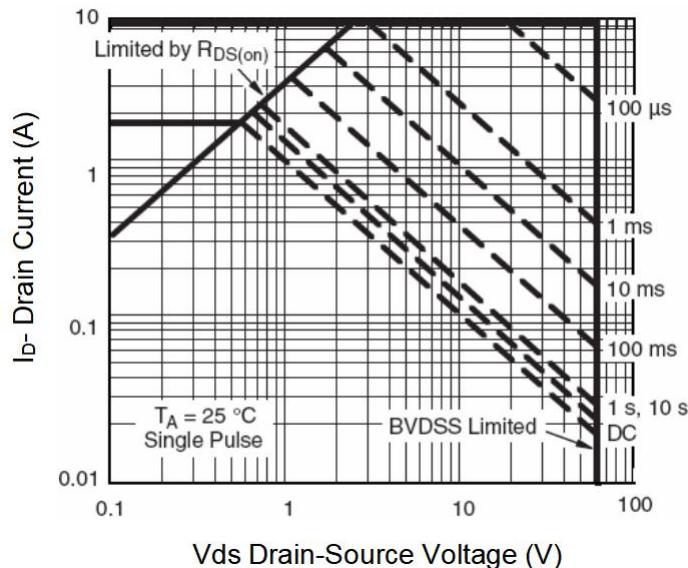
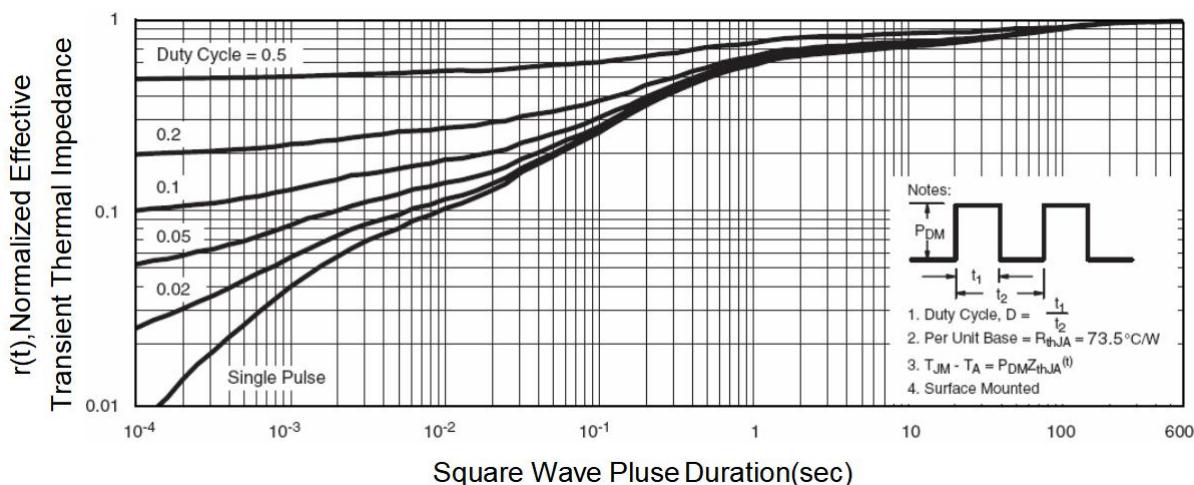
Note 2. Surface Mounted on FR4 Board, t ≤ 10 sec.

Note 3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

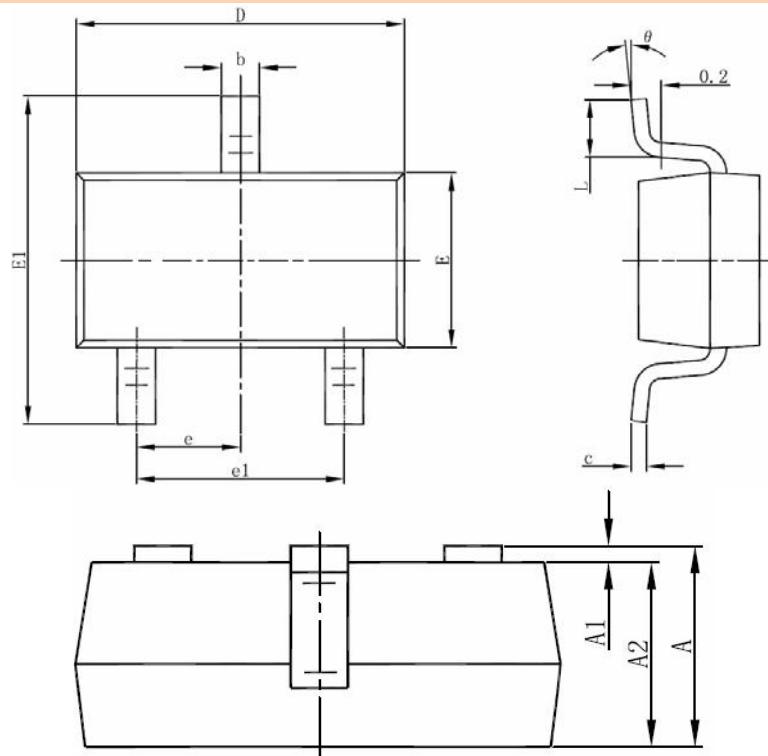
Note 4. Guaranteed by design, not subject to production


**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**
**Figure 1. Switching Test Circuit**

**Figure 2. Switching Waveforms**

**Figure 3. Power Dissipation**

**Figure 4. Drain Current**

**Figure 5. Output Characteristics**

**Figure 6. Drain-Source On-Resistance**



**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**
**Figure 7. Transfer Characteristics**

**Figure 8. Drain-Source On-Resistance**

**Figure 9.  $R_{dson}$  vs  $V_{gs}$** 

**Figure 10. Capacitance vs  $V_{ds}$** 

**Figure 11. Gate Charge**

**Figure 12. Source- Drain Diode Forward**



**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**
**Figure 13. Safe Operation Area**

**Figure 14. Normalized Maximum Transient Thermal Impedance**


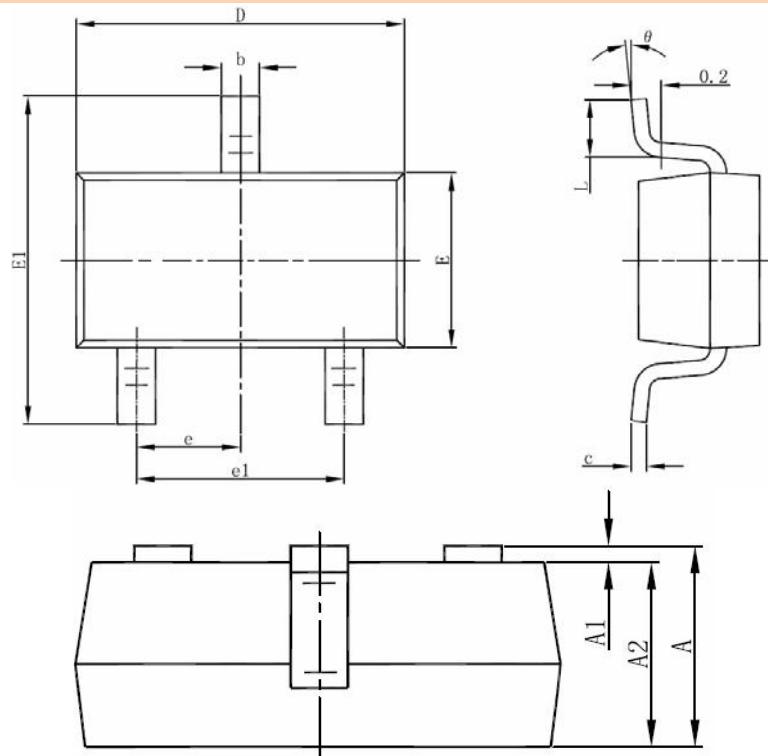
## PACKAGE INFORMATION

**SOT-23-3L**


Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

## PACKAGE INFORMATION

### SOT-23



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°